

SiC MOSFET

CoolSiC™ MOSFET 650 V G2

Built on Infineon's robust 2nd generation Silicon Carbide trench technology, the 650 V CoolSiC™ MOSFET delivers unparalleled performance, superior reliability, and great ease of use. It enables cost effective, highly efficient, and simplified designs to fulfill the ever-growing system and market needs.

Features

- Ultra-low switching losses
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.5\text{ V}$
- Robust against parasitic turn-on even with 0 V turn-off gate voltage
- Flexible driving voltage and compatible with bipolar driving scheme
- Robust body diode operation under hard commutation events
- .XT interconnection technology for best-in-class thermal performance

Benefits

- Enables high efficiency and high power density designs
- Facilitates great ease of use and integration
- Provides the best price performance ratio compared to Industry's most ambitious roadmaps
- Reduces the size, weight and bill of materials of the systems
- Enhances system robustness and reliability

Potential applications

- SMPS
- Solar PV inverters
- Energy storage and battery formation
- UPS
- EV charging infrastructure
- Motor drives

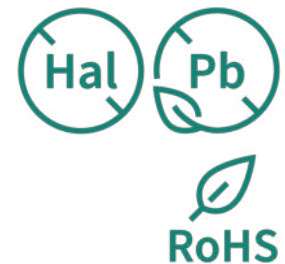
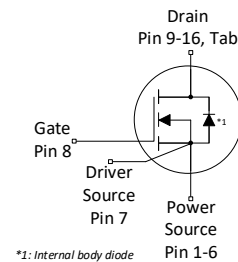
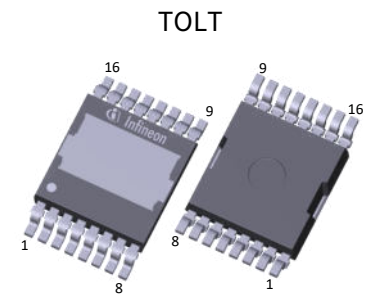
Product validation

Fully qualified according to JEDEC for Industrial Applications

Please note: The source and driver source pins are not exchangeable. Their exchange might lead to malfunction.

Table 1 Key performance parameters

Parameter	Value	Unit
V_{DSS} over full $T_{j,range}$	650	V
$R_{DS(on),typ}$	60	mΩ
$R_{DS(on),max}$	73	mΩ
$Q_{G,typ}$	18	nC
$I_{D,pulse}$	96	A
$Q_{oss} @ 400\text{ V}$	36	nC
$E_{oss} @ 400\text{ V}$	4.8	μJ



Type / Ordering code	Package	Marking	Related links
IMLT65R060M2H	PG-HDSOP-16	65R060M2	see Appendix A



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1 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified.

Note: for optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous DC drain current ¹⁾	I_{DDC}	-	-	40 28	A	$T_c = 25\text{ °C}$ $T_c = 100\text{ °C}$
Peak drain current ²⁾	I_{DM}	-	-	96	A	$T_c = 25\text{ °C}$, $V_{\text{GS}} = 18\text{ V}$
Avalanche energy, single pulse	E_{AS}	-	-	89	mJ	$I_D = 3.4\text{ A}$, $V_{\text{DD}} = 50\text{ V}$; see table 11
Avalanche energy, repetitive	E_{AR}	-	-	0.44	mJ	
Avalanche current, single pulse	I_{AS}	-	-	3.4	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	200	V/ns	$V_{\text{DS}} = 0\ldots 400\text{ V}$
Gate source voltage (static) ³⁾	V_{GS}	-7	-	23	V	-
Gate source voltage (transient)	V_{GS}	-10	-	25	V	$t_p \leq 500\text{ ns}$, duty cycle $\leq 1\%$
Power dissipation	P_{tot}	-	-	200	W	$T_c = 25\text{ °C}$
Storage temperature	T_{stg}	-55	-	150	°C	-
Operating junction temperature	T_j	-55	-	175	°C	
Mounting torque	-	-	-	-	Ncm	
Continuous reverse drain current ¹⁾	I_{SDC}	-	-	40 28	A	$V_{\text{GS}} = 18\text{ V}$, $T_c = 25\text{ °C}$ $V_{\text{GS}} = 0\text{ V}$, $T_c = 25\text{ °C}$
Peak reverse drain current ²⁾	I_{SM}	-	-	96 29	A	$T_c = 25\text{ °C}$, $t_p \leq 250\text{ ns}$ $T_c = 25\text{ °C}$
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_c = 25\text{ °C}$, $t = 1\text{ min}$

¹⁾ Limited by $T_{j,\text{max}}$.

²⁾ Pulse width t_{pulse} limited by $T_{j,\text{max}}$.

³⁾ The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{th(j-c)}$	-	-	0.75	°C/W	Not subject to production test. Parameter verified by design/characterization according to JESD51-14.
Soldering temperature, reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

3 Operating range

Table 4 **Operating range**

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Recommended turn-on voltage	$V_{GS(on)}$	-	18	-	V	-
Recommended turn-off voltage	$V_{GS(off)}$	-	0	-	V	

4 Electrical characteristics

at $T_j = 25\text{ °C}$, unless otherwise specified

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source voltage	V_{DS}	650	-	-	V	$V_{GS} = 0\text{ V}$, $I_D = 0.31\text{ mA}$
Gate threshold voltage ⁴⁾	$V_{GS(th)}$	3.5	4.5	5.6	V	$V_{DS} = V_{GS}$, $I_D = 3.1\text{ mA}$
Zero gate voltage drain current	I_{DSS}	-	1 3	75 -	μA	$V_{DS} = 650\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ °C}$ $V_{DS} = 650\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 175\text{ °C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	78 60 55 98	- 73 - -	$\text{m}\Omega$	$V_{GS} = 15\text{ V}$, $I_D = 15.4\text{ A}$, $T_j = 25\text{ °C}$ $V_{GS} = 18\text{ V}$, $I_D = 15.4\text{ A}$, $T_j = 25\text{ °C}$ $V_{GS} = 20\text{ V}$, $I_D = 15.4\text{ A}$, $T_j = 25\text{ °C}$ $V_{GS} = 18\text{ V}$, $I_D = 15.4\text{ A}$, $T_j = 175\text{ °C}$
Internal gate resistance	$R_{G,int}$	-	5.1	-	Ω	$f = 1\text{ MHz}$

⁴⁾ Tested after 1 ms pulse at $V_{GS} = +20\text{ V}$. "Linear mode" operation is not recommended. For assessment of potential "linear mode" operation, please contact Infineon sales office.

Table 6 Dynamic characteristics

External parasitic elements (PCB layout) influence switching behavior significantly.

Stray inductances and coupling capacitances must be minimized.

For layout recommendations please use provided application notes or contact Infineon sales office.

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	669	-	pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 400\text{ V}$, $f = 250\text{ kHz}$
Reverse transfer capacitance	C_{rss}	-	4.1	-	pF	
Output capacitance ⁵⁾	C_{oss}	-	50	65	pF	
Output charge ⁵⁾	Q_{oss}	-	36	46	nC	calculation based on C_{oss}
Effective output capacitance, energy related ⁶⁾	$C_{o(er)}$	-	60	-	pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 0...400\text{ V}$
Effective output capacitance, time related ⁷⁾	$C_{o(tr)}$	-	89	-	pF	$I_D = \text{constant}$, $V_{GS} = 0\text{ V}$, $V_{DS} = 0...400\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	6.3	-	ns	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 15.4\text{ A}$, $R_{G,ext} = 1.8\text{ }\Omega$; see table 10
Rise time	t_r	-	5.6	-	ns	
Turn-off delay time	$t_{d(off)}$	-	13.7	-	ns	
Fall time	t_f	-	4.8	-	ns	

Table 6 Dynamic characteristics

External parasitic elements (PCB layout) influence switching behavior significantly.
 Stray inductances and coupling capacitances must be minimized.
 For layout recommendations please use provided application notes or contact Infineon sales office.

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Turn-ON switching losses ⁸⁾	E_{on}	-	26	-	μJ	$V_{DD} = 400\text{ V}$, $V_{GS} = 0/18\text{ V}$, $I_D = 15.4\text{ A}$, $R_{G,ext} = 1.8\text{ }\Omega$
Turn-OFF switching losses ⁸⁾	E_{off}	-	13	-	μJ	
Total switching losses ⁸⁾	E_{tot}	-	39	-	μJ	

⁵⁾ Maximum specification is defined by calculated six sigma upper confidence bound

⁶⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400 V.

⁷⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400 V.

⁸⁾ MOSFET used in half-bridge configuration without external diode

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Plateau gate to source charge	$Q_{GS(pl)}$	-	4.9	-	nC	$V_{DD} = 400\text{ V}$, $I_D = 15.4\text{ A}$, $V_{GS} = 0\text{ to }18\text{ V}$
Gate to drain charge	Q_{GD}	-	3.4	-	nC	
Total gate charge	Q_G	-	18	-	nC	

Table 8 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source reverse voltage	V_{SD}	-	4.3	-	V	$V_{GS} = 0\text{ V}$, $I_S = 15.4\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$
MOSFET forward recovery time	t_{fr}	-	11.3 7.4	-	ns	$V_{DD} = 400\text{ V}$, $I_S = 15.4\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$; see table 9 $V_{DD} = 400\text{ V}$, $I_S = 15.4\text{ A}$, $di_S/dt = 4000\text{ A}/\mu\text{s}$; see table 9
MOSFET forward recovery charge ⁹⁾	Q_{fr}	-	38 50	-	nC	$V_{DD} = 400\text{ V}$, $I_S = 15.4\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$; see table 9 $V_{DD} = 400\text{ V}$, $I_S = 15.4\text{ A}$, $di_S/dt = 4000\text{ A}/\mu\text{s}$; see table 9
MOSFET peak forward recovery current	I_{frm}	-	6.7 13.5	-	A	$V_{DD} = 400\text{ V}$, $I_S = 15.4\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$; see table 9 $V_{DD} = 400\text{ V}$, $I_S = 15.4\text{ A}$, $di_S/dt = 4000\text{ A}/\mu\text{s}$; see table 9

⁹⁾ Q_{fr} includes Q_{oss}

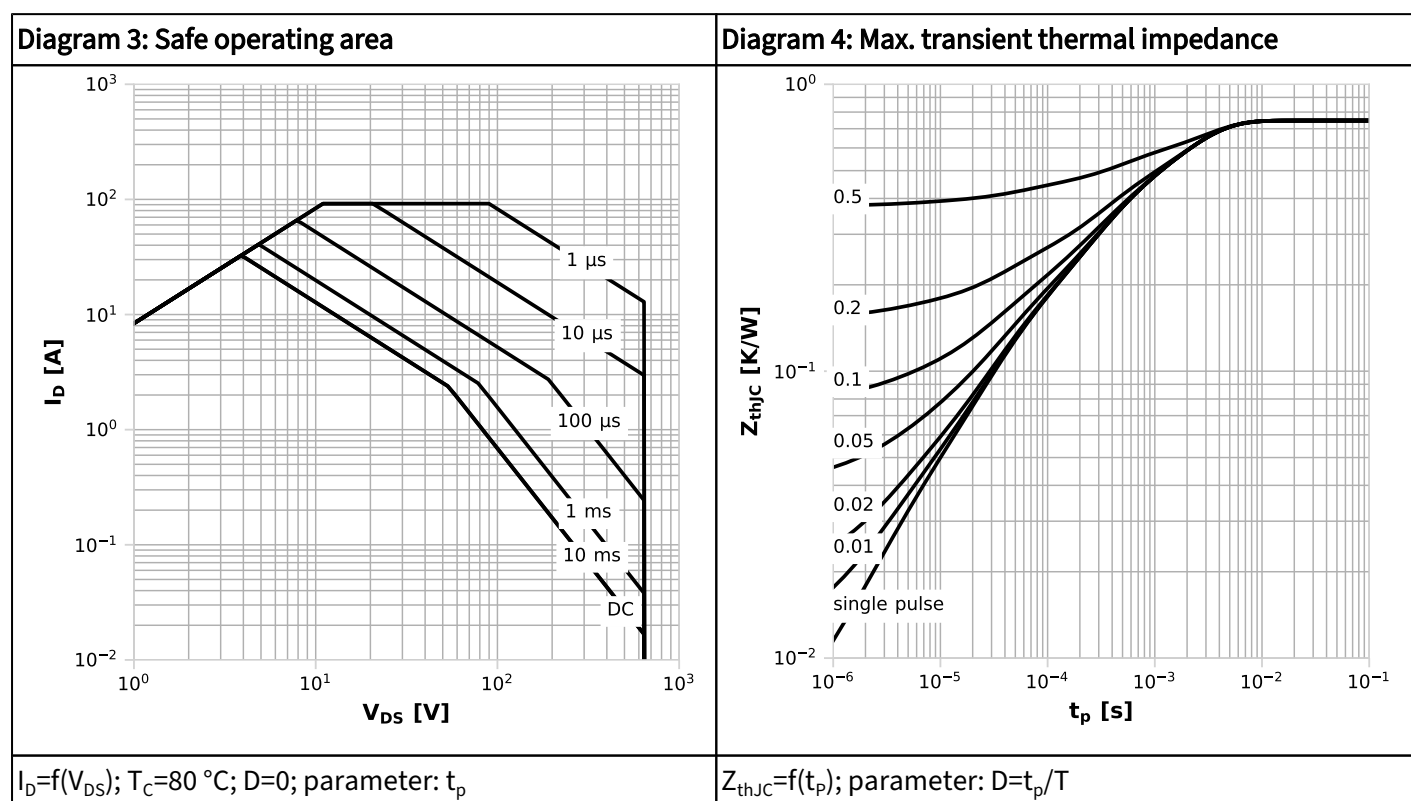
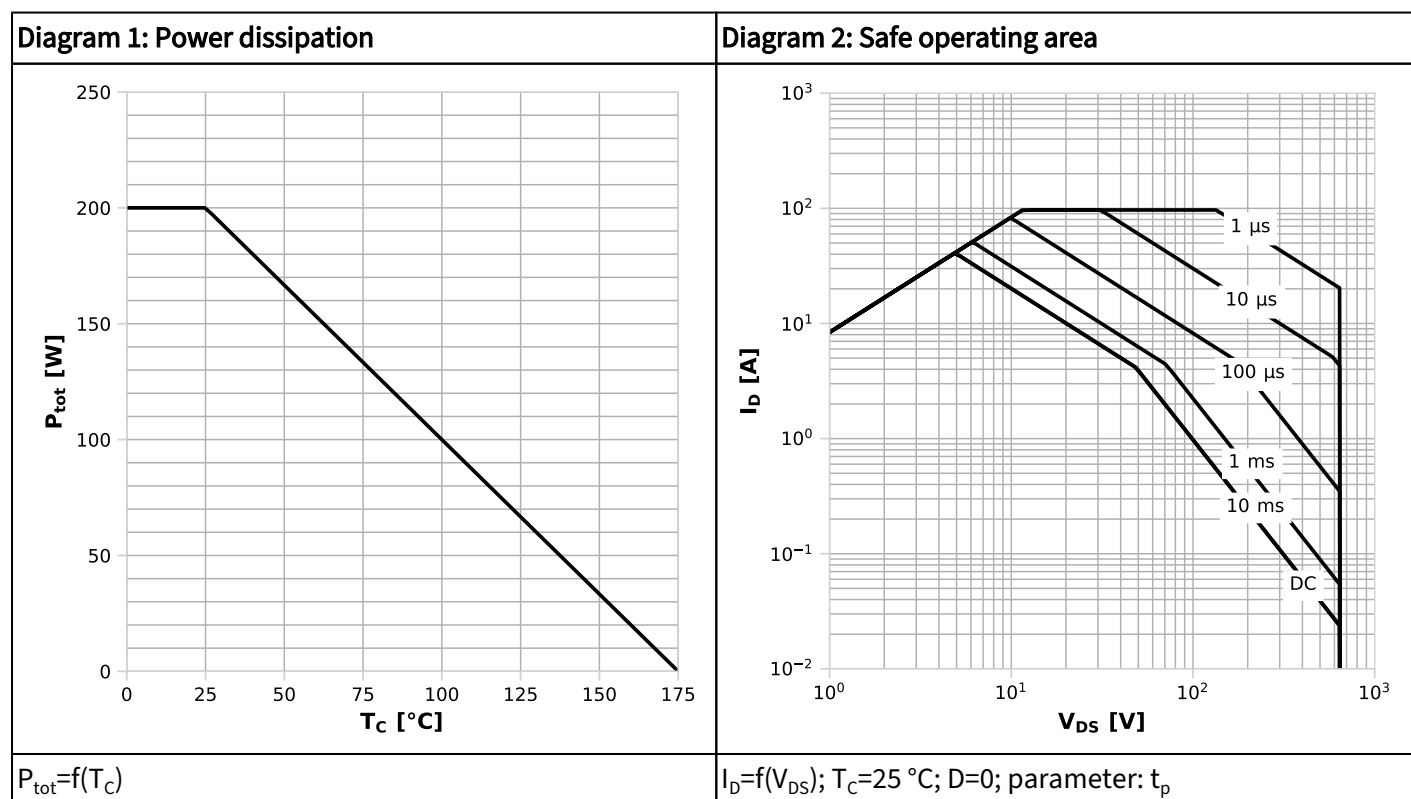
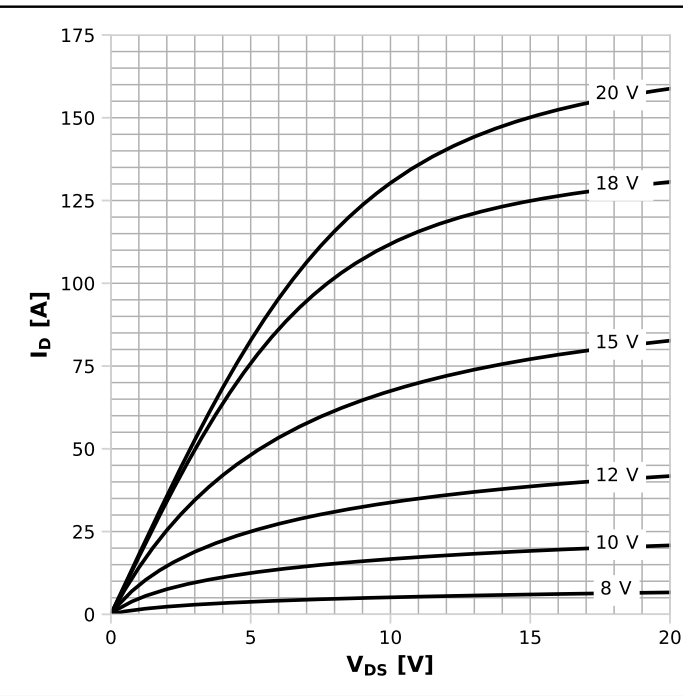
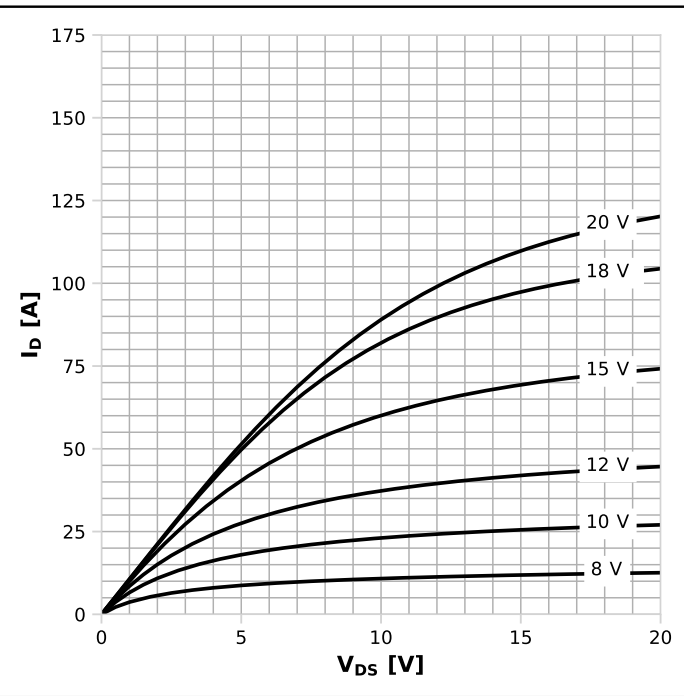


Diagram 5: Typ. output characteristics



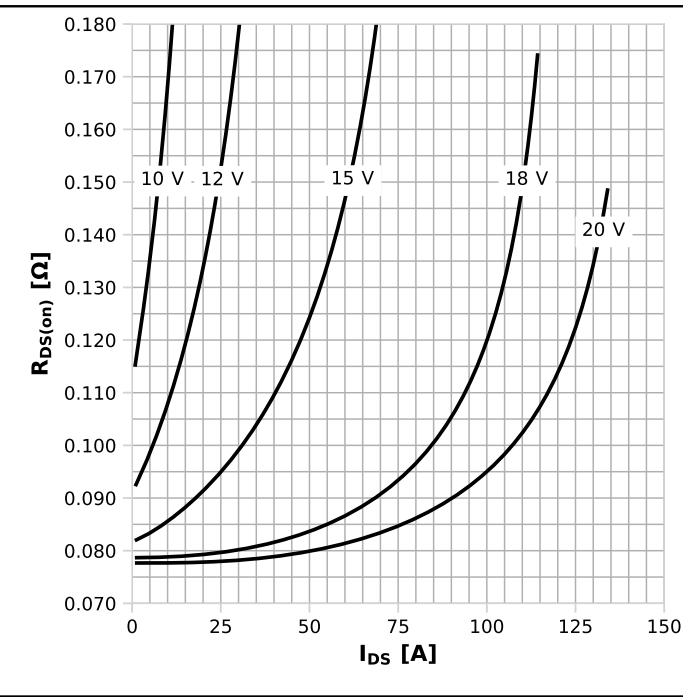
$I_D = f(V_{DS})$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



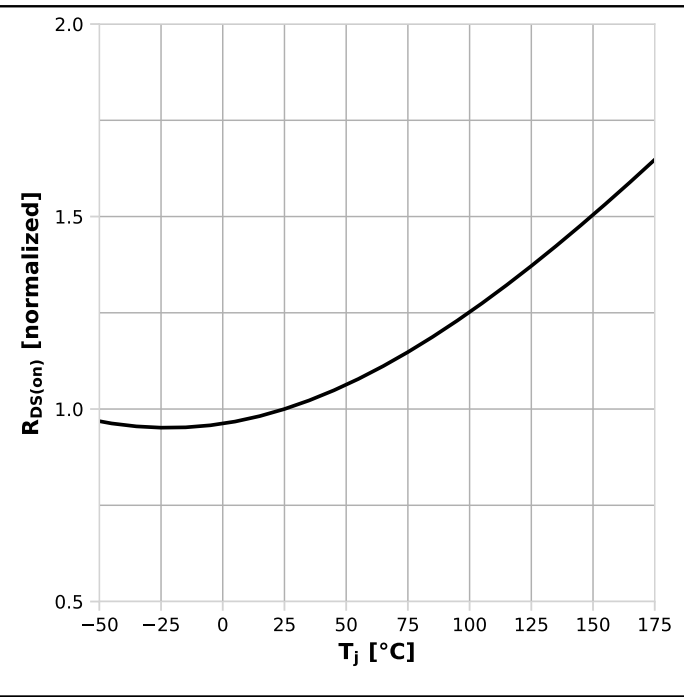
$I_D = f(V_{DS})$; $T_j = 175\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



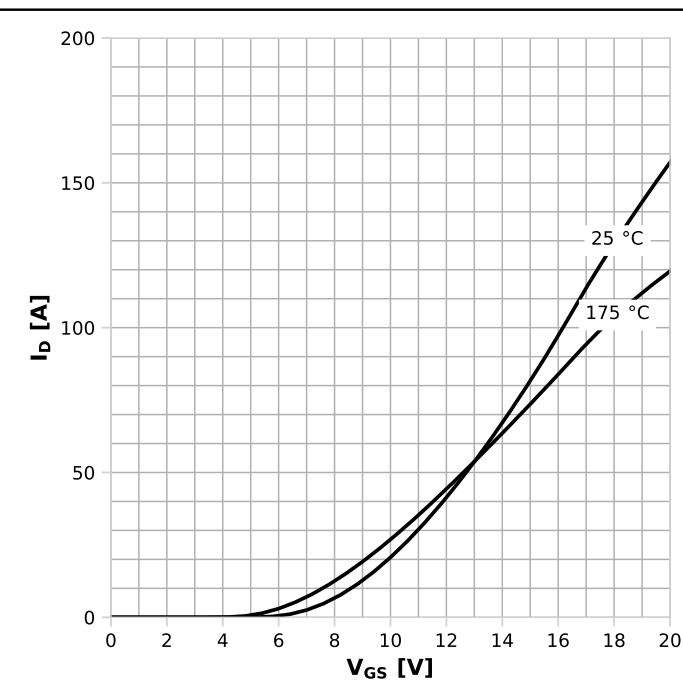
$R_{DS(on)} = f(I_D)$; $T_j = 125\text{ °C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



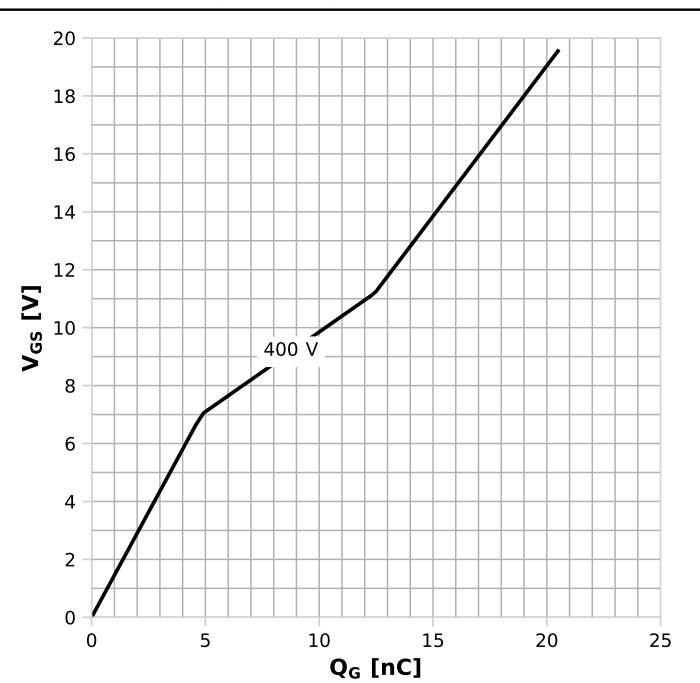
$R_{DS(on)} = f(T_j)$; $I_D = 15.4\text{ A}$; $V_{GS} = 18\text{ V}$

Diagram 9: Typ. transfer characteristics



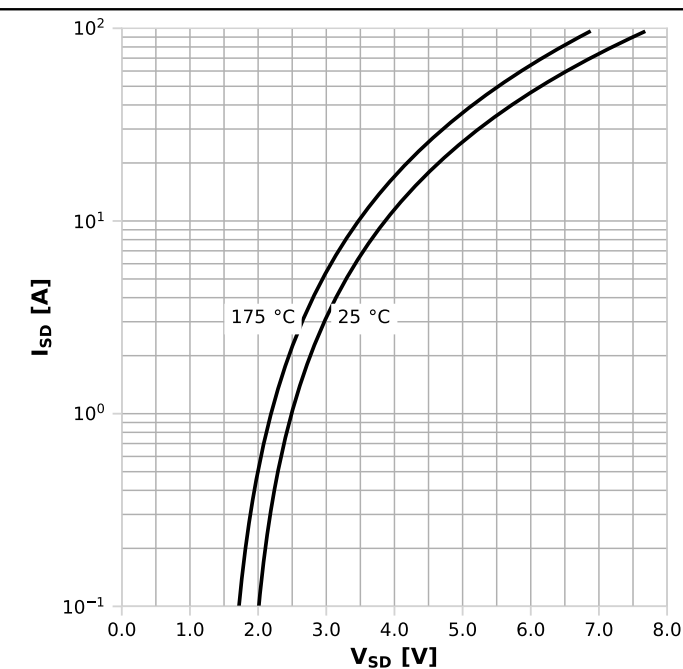
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 10: Typ. gate charge



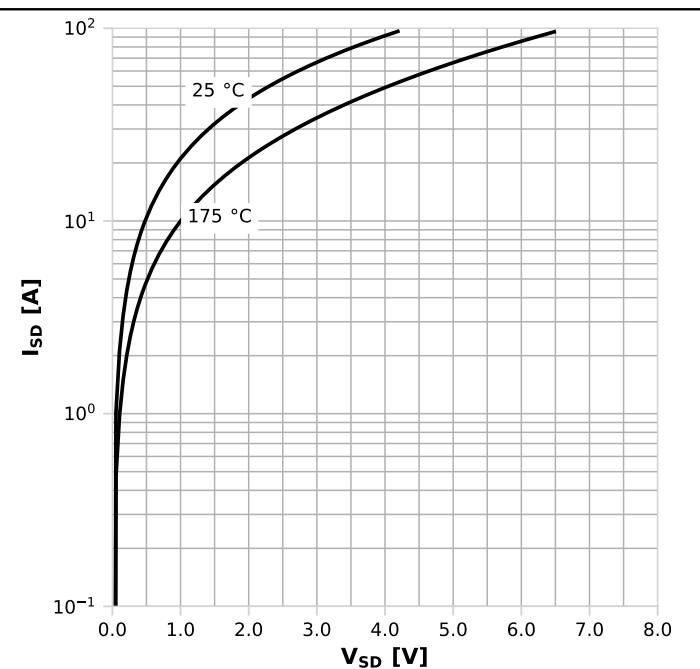
$V_{GS} = f(Q_{gate})$; $I_D = 15.4$ A pulsed; parameter: V_{DD}

Diagram 11: Typ. reverse characteristics



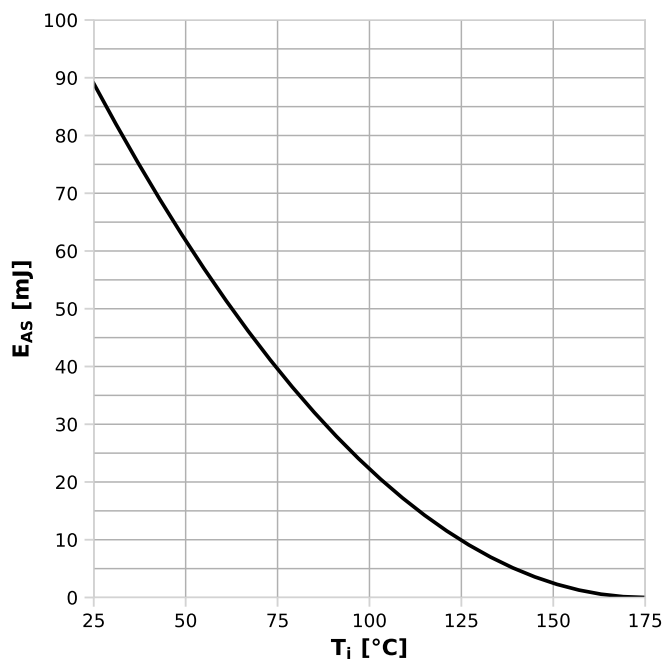
$I_{SD} = f(V_{SD})$; $V_{GS} = 0$ V; parameter: T_j

Diagram 12: Typ. reverse characteristics



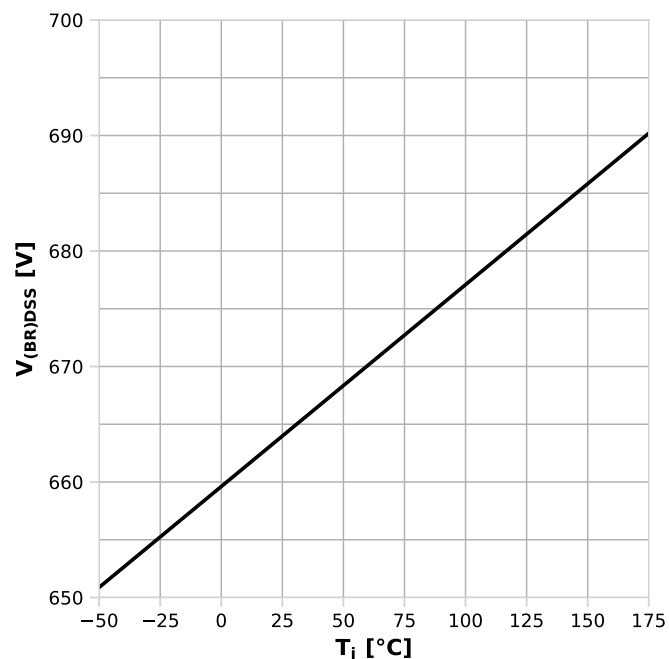
$I_{SD} = f(V_{SD})$; $V_{GS} = 18$ V; parameter: T_j

Diagram 13: Avalanche energy



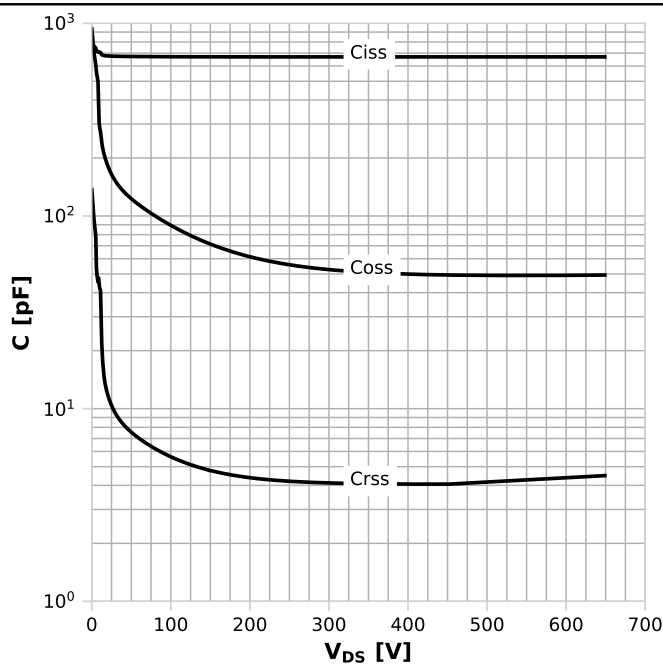
$E_{AS}=f(T_j)$; $I_D=3.4$ A; $V_{DD}=50$ V

Diagram 14: Drain-source breakdown voltage



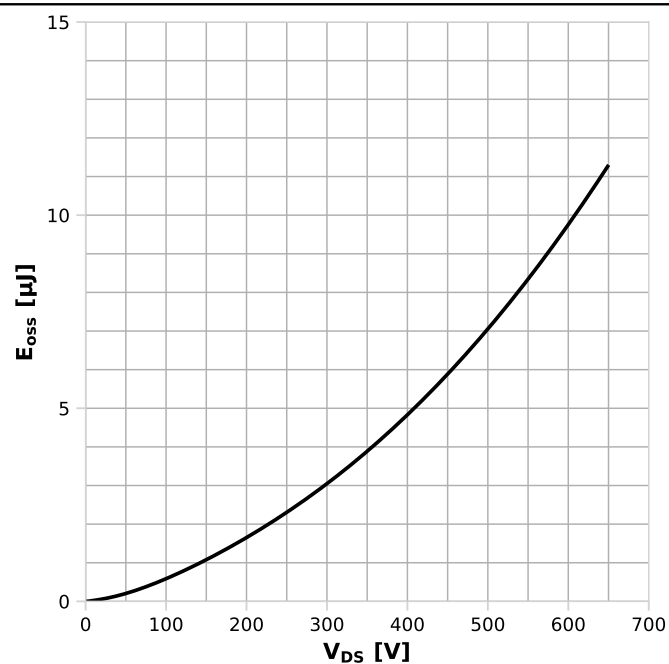
$V_{(BR)DSS}=f(T_j)$; $I_D=0.31$ mA

Diagram 15: Typ. capacitances



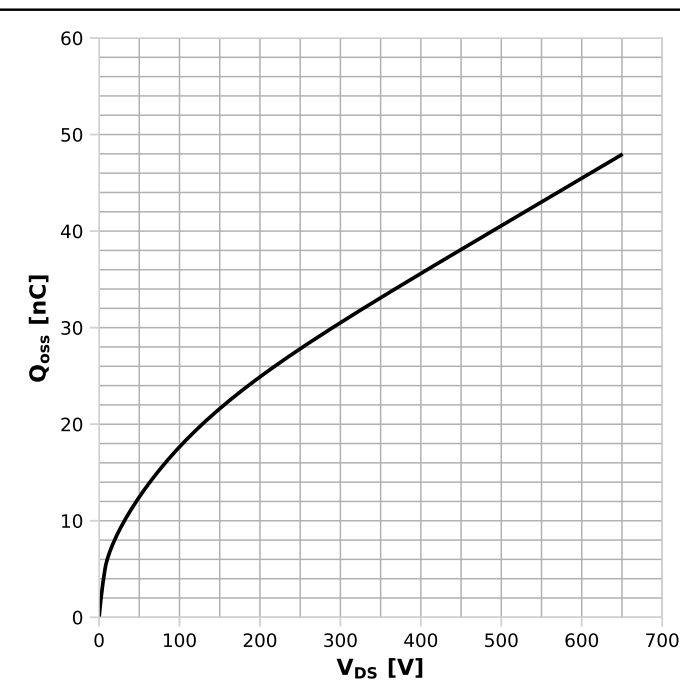
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=250$ kHz

Diagram 16: Typ. Coss stored energy



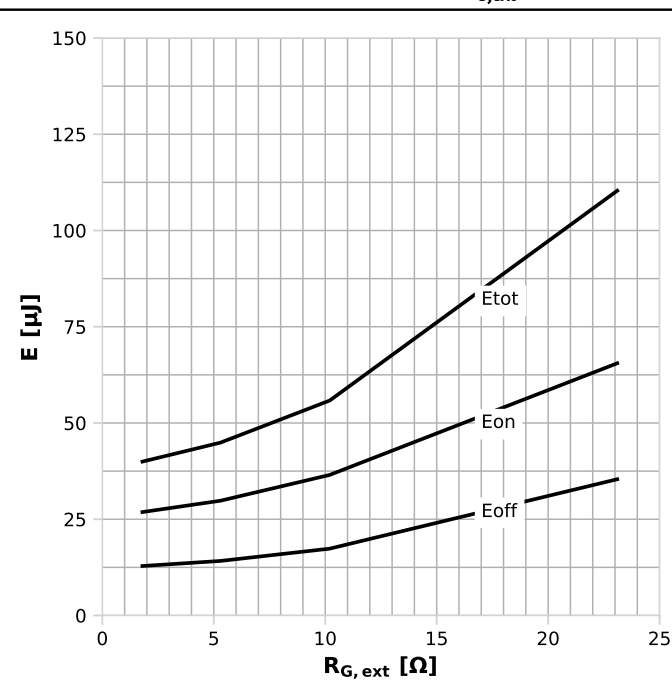
$E_{oss}=f(V_{DS})$

Diagram 17: Typ. Qoss output charge



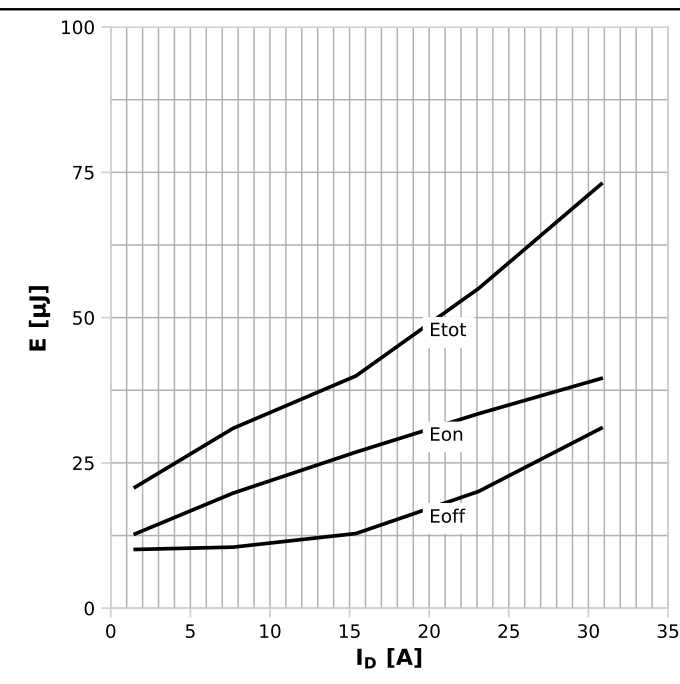
$Q_{oss}=f(V_{DS})$

Diagram 18: Typ. Switching Losses vs $R_{G,ext}$



$E=f(R_{G,ext}); V_{DD}=400\text{ V}; V_{GS}=0-18\text{ V}; I_D=15.4\text{ A}$

Diagram 19: Typ. Switching Losses vs switching current



$E=f(I_D); V_{DD}=400\text{ V}; V_{GS}=0-18\text{ V}; R_{G,ext}=1.8\ \Omega$

6 Test circuits

Table 9 Body diode characteristics

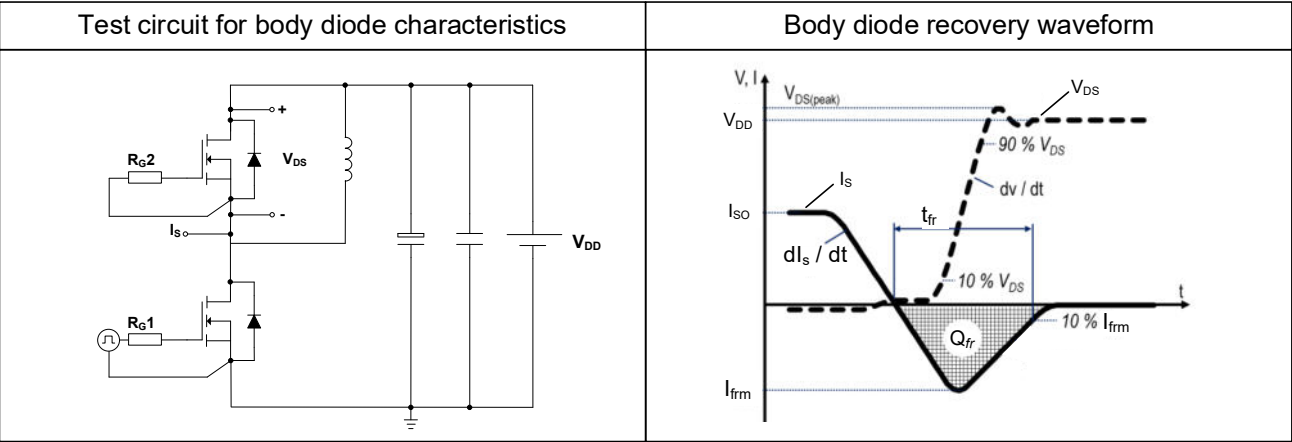


Table 10 Switching times

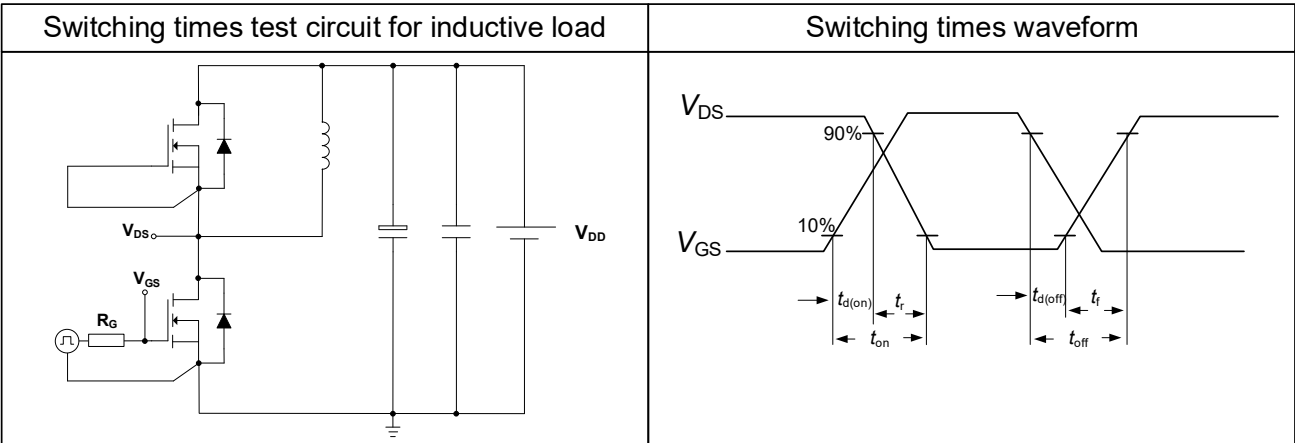
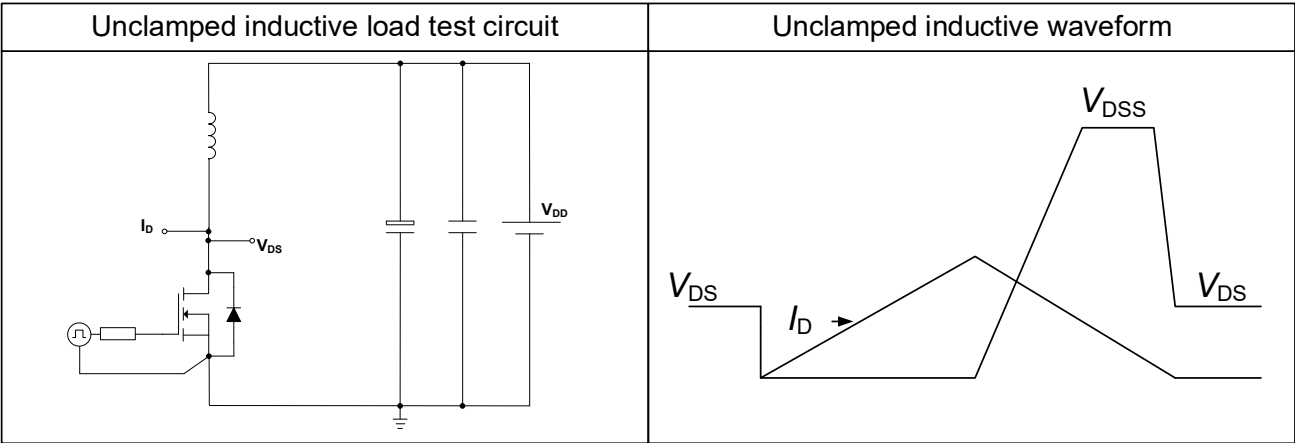


Table 11 Unclamped inductive load



7 Package outlines

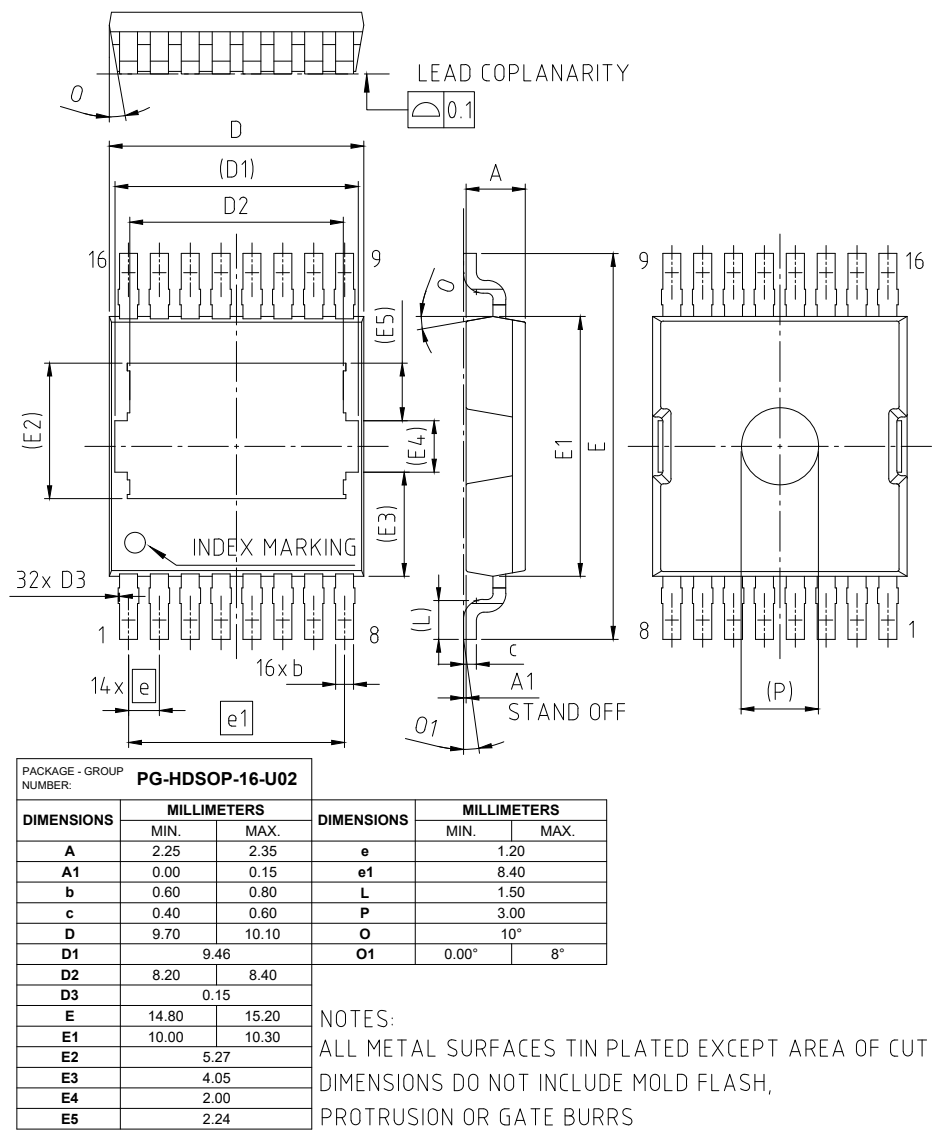


Figure 1 Outline PG-HDSOP-16, dimensions in mm

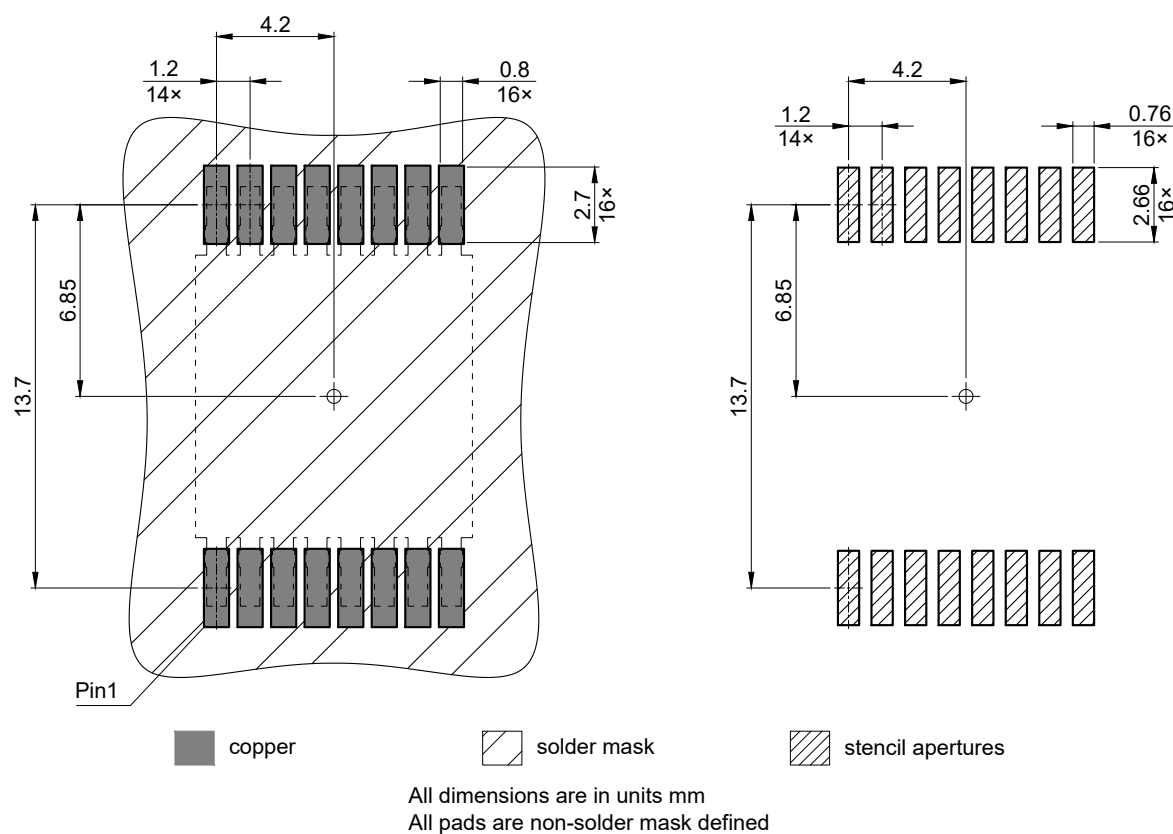
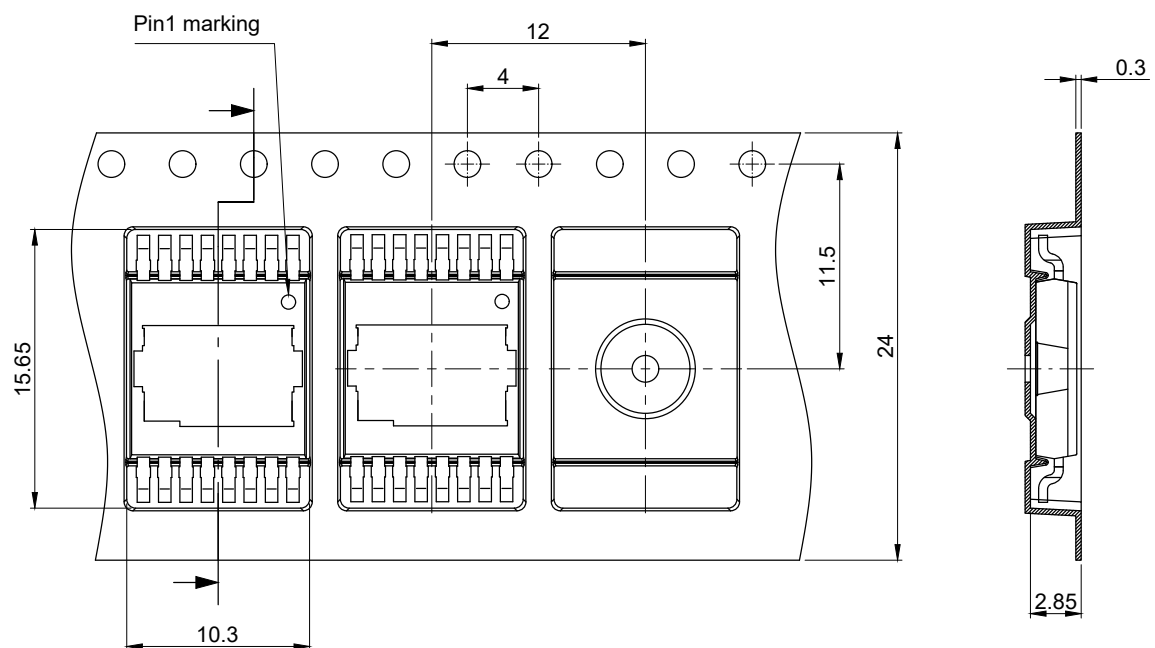


Figure 2 Footprint drawing PG-HDSOP-16, dimensions in mm



All dimensions are in units mm

The drawing is in compliance with ISO 128-30, Projection Method 1 []

Figure 3 Packaging variant PG-HDSOP-16, dimensions in mm

8 Appendix A

Table 12 **Related links**

- [IFX CoolSiC CoolSiC™ MOSFET 650 V G2 Webpage](#)
- [IFX CoolSiC CoolSiC™ MOSFET 650 V G2 Application Note](#)
- [IFX CoolSiC CoolSiC™ MOSFET 650 V G2 Simulation Model](#)
- [IFX Design tools](#)

Revision history

IMLT65R060M2H

Revision 2024-11-20, Rev. 2.1

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2024-05-03	Release of final
2.1	2024-11-20	update of reverse diode characteristics

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